



Silicon Microstrip R&D at SCIPP and the University of California at Santa Cruz

**Future Linear Colliders Spanish Network
Universidad de Sevilla**

10-12 February 2014

**Bruce Schumm
UC Santa Cruz / SCIPP**

The SCIPP/UCSC SiLC/SiD GROUP

(Harwdare R&D Participants)

Faculty/Senior

Vitaliy Fadeyev
Bruce Schumm

Students

Wyatt Crockett
Conor Timlin
Spencer Ramirez
Christopher Milke
Olivia Johnson

More Students

Vivian Tang
Reyer Band
George Courcoubetis
Bryce Burgess

Lead Engineer: Ned Spencer

Technical Staff: Max Wilder, Forest Martinez-McKinney

All participants are mostly working on other things
(ATLAS, biophysics, classes...)

Students are undergraduates from physics and engineering

FOCUS AND MILESTONES OF SCIPP GROUP

Activity 1: Development of long ladder and forward strip applications (THIS TALK!)

- Front-end electronics (LSTFE ASIC)
- Exploration of sensor requirements and length limitations for long ladders (NIM-A 729 p127 (2013))

Activity 2: Development of far-forward calorimetry (NOT THIS TALK!)

- Radiation damage studies
- Detector optimization
- Physics studies

The LSTFE ASIC

- Optimized for long ($\sim 1\text{m}$) ladders but also appropriate for high-occupancy short strip application
- Uses time-over threshold analog response \rightarrow limited dead time without loss of resolution
- Simple re-optimization would further improve data throughput rate for high-occupancy use
- 128-channel prototype (LSTFE-2) under testing in lab (but a bit fallow)

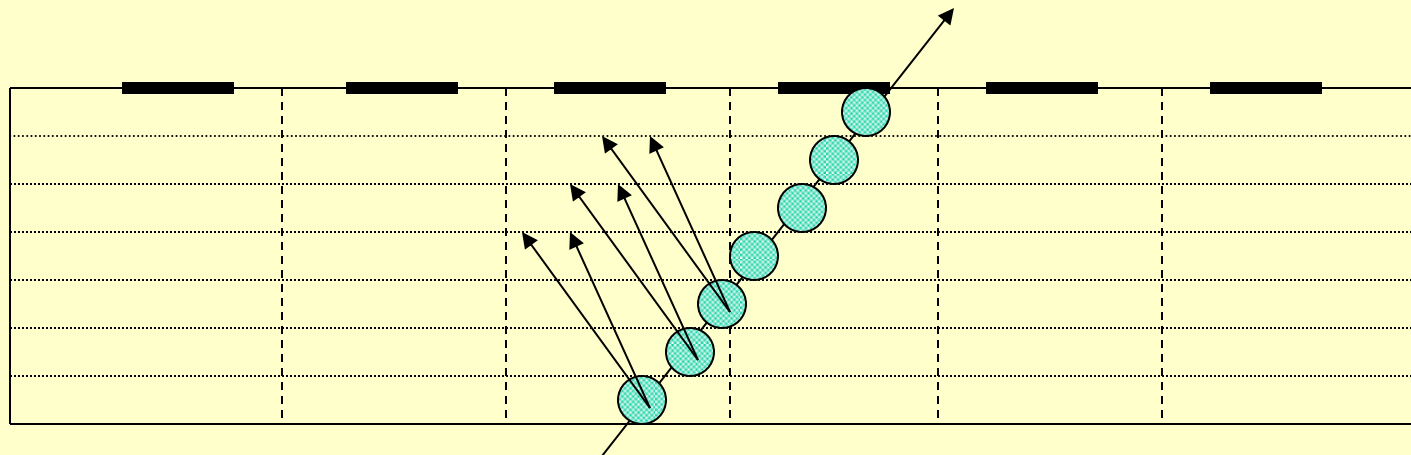
Now for the details...

Pulse Development Simulation

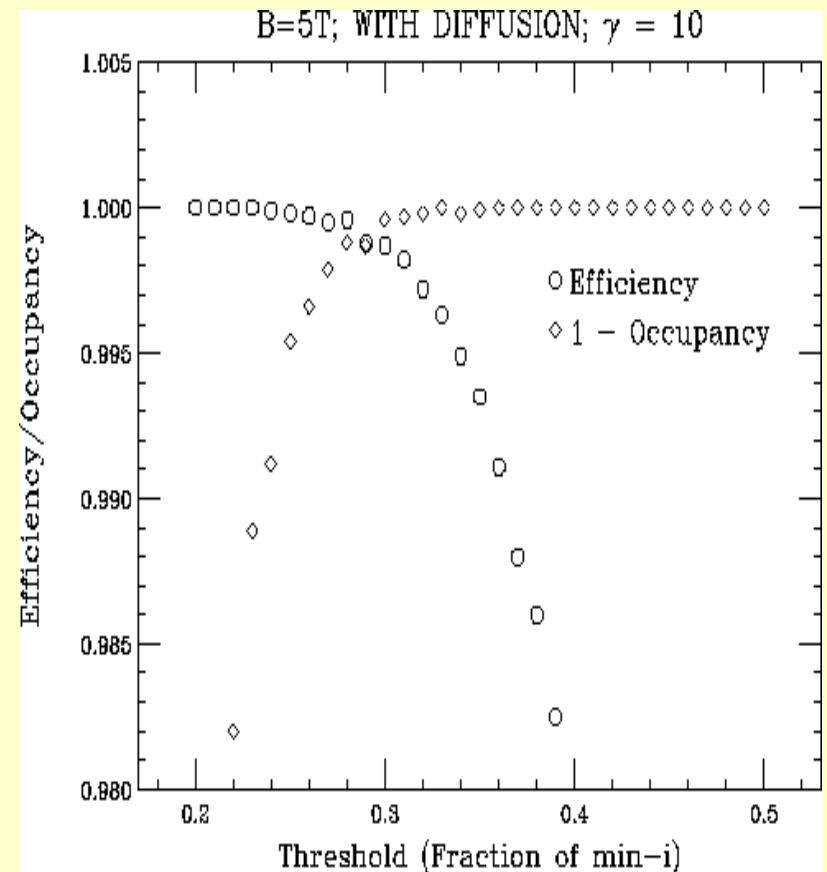
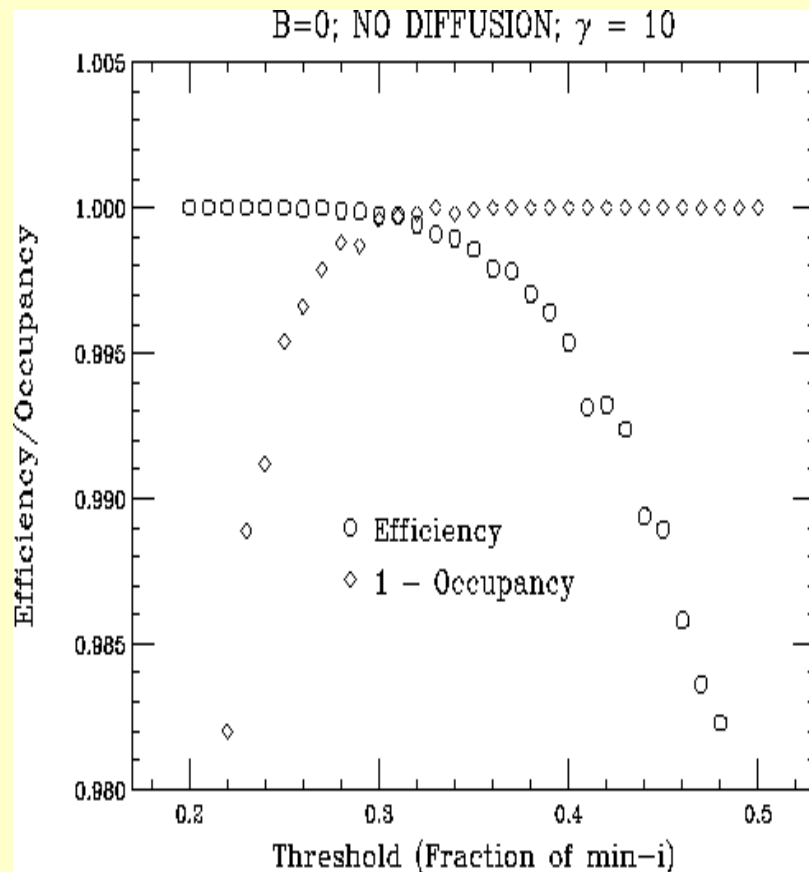
Christian Flacco & Michael Young (Grads); John Mikelich (Undergrad)

Long Shaping-Time Limit: strip sees signal if and only if hole is collected onto strip (no electrostatic coupling to neighboring strips)

Include: Landau deposition (SSSimSide; Gerry Lynch LBNL), variable geometry, Lorentz angle, carrier diffusion, electronic noise and digitization effects



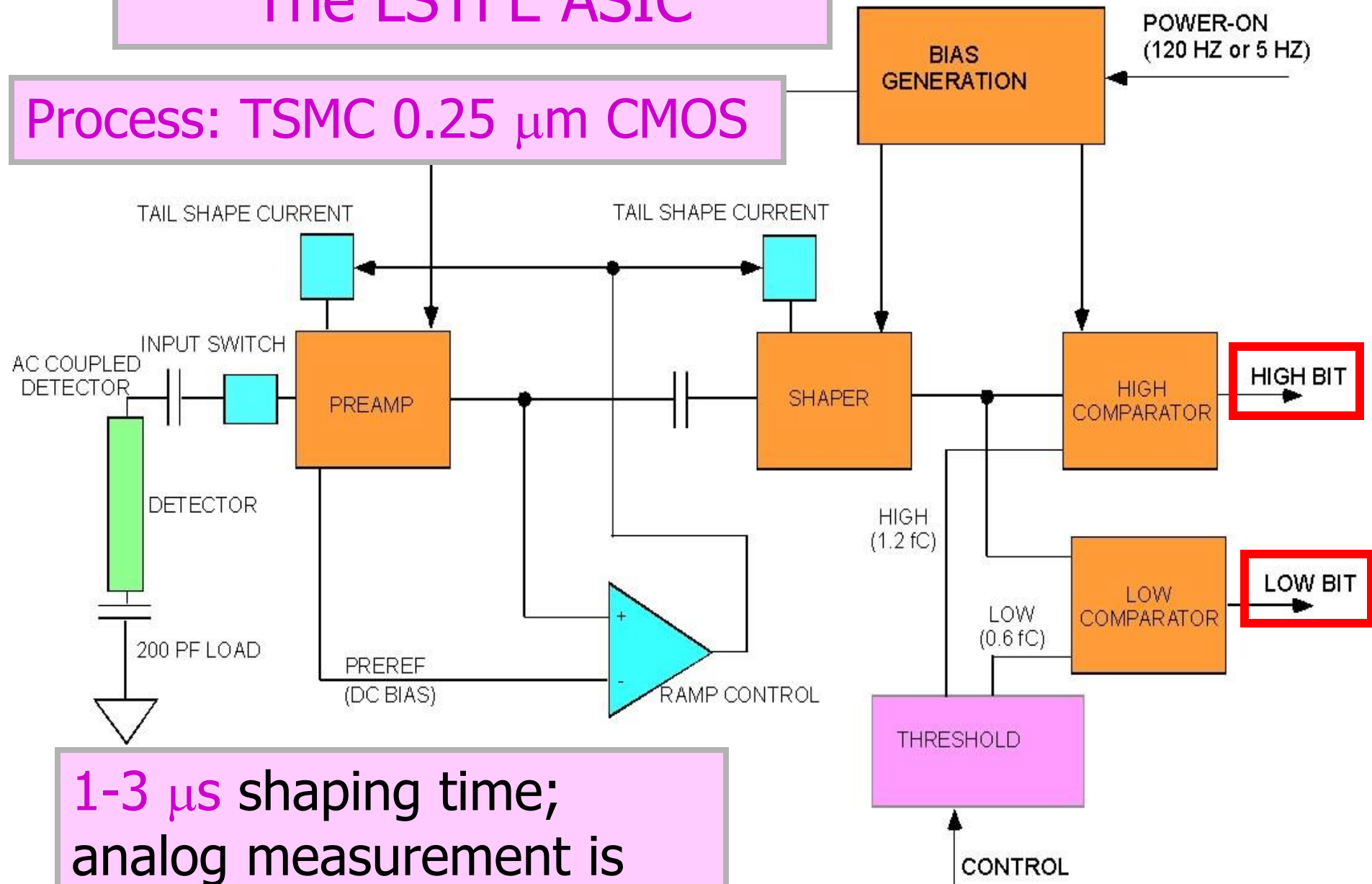
Simulation Result: S/N for 167 cm Ladder (capacitive noise only)



Simulation suggests that long-ladder operation is feasible

The LSTFE ASIC

Process: TSMC 0.25 μm CMOS

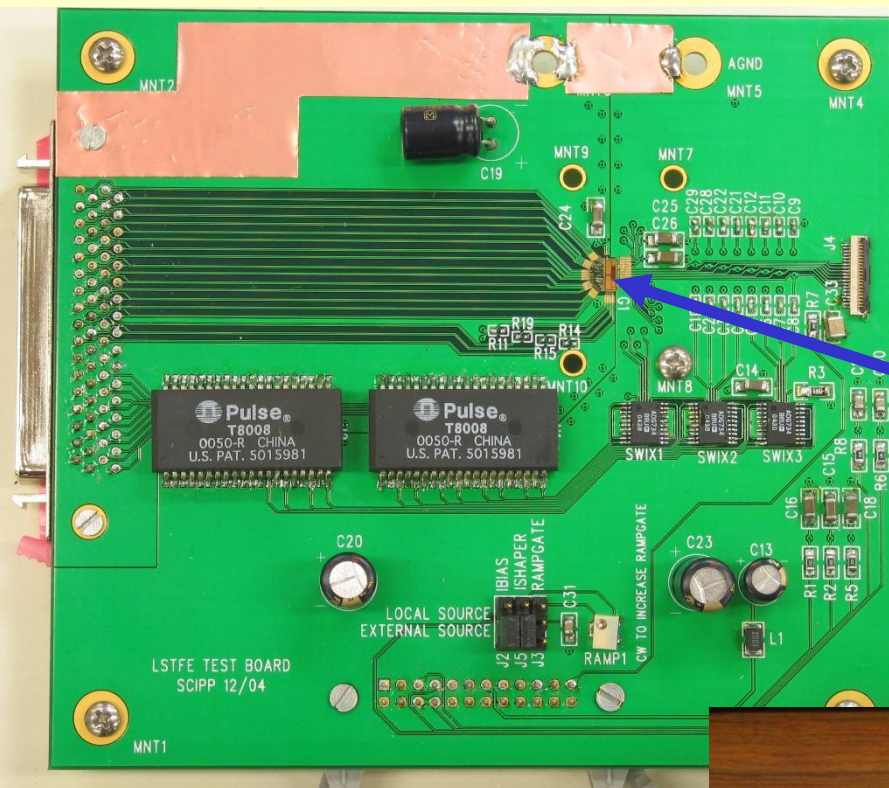


1-3 μs shaping time;
analog measurement is
Time-Over-Threshold

INITIAL RESULTS

LSTFE chip
mounted on readout
board

FPGA-based
control and data-
acquisition system



Comparator S Curves

Vary threshold for given input charge

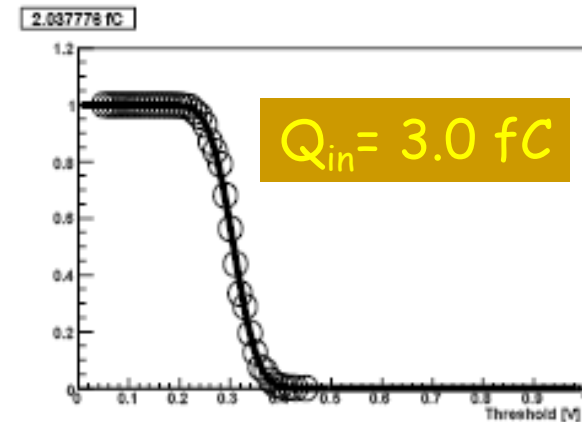
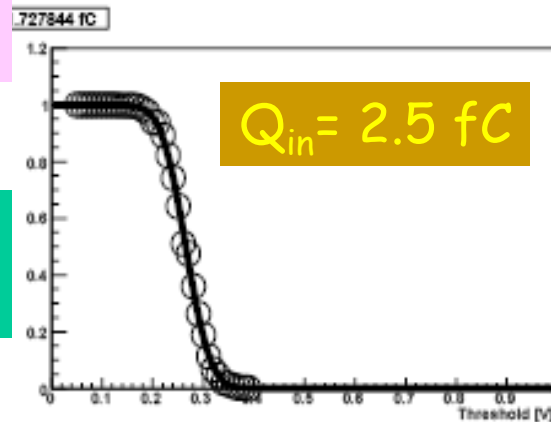
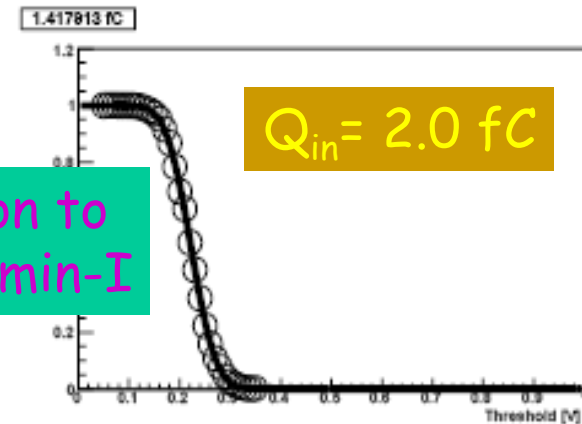
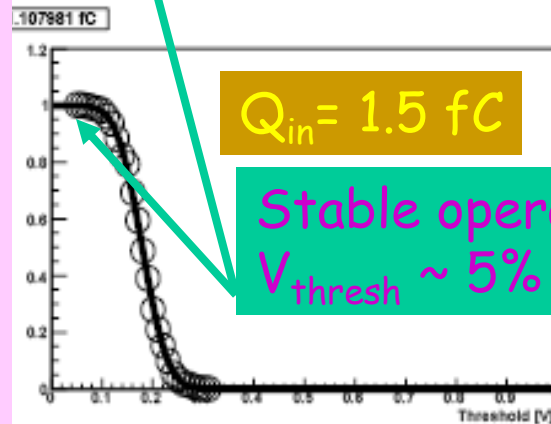
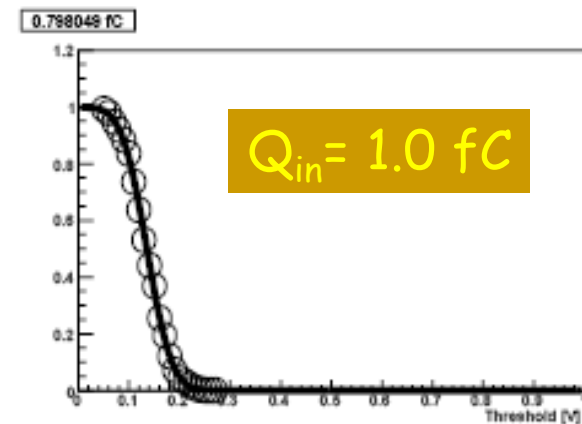
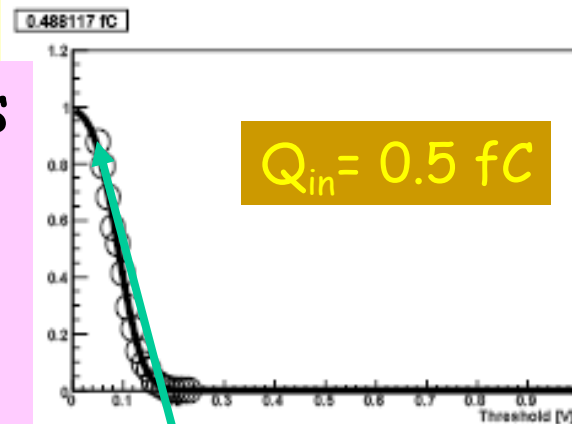
Read out system with FPG-based DAQ

Get

$1 - \text{erf}(\text{threshold})$

with 50% point giving response, and width giving noise

Hi/Lo comparators function independently



Stable operation to $V_{\text{thresh}} \sim 5\%$ of min-I

EQUIVALENT CAPACITANCE STUDY

Noise vs. Capacitance (at $\tau_{\text{shape}} = 1.2 \mu\text{s}$)

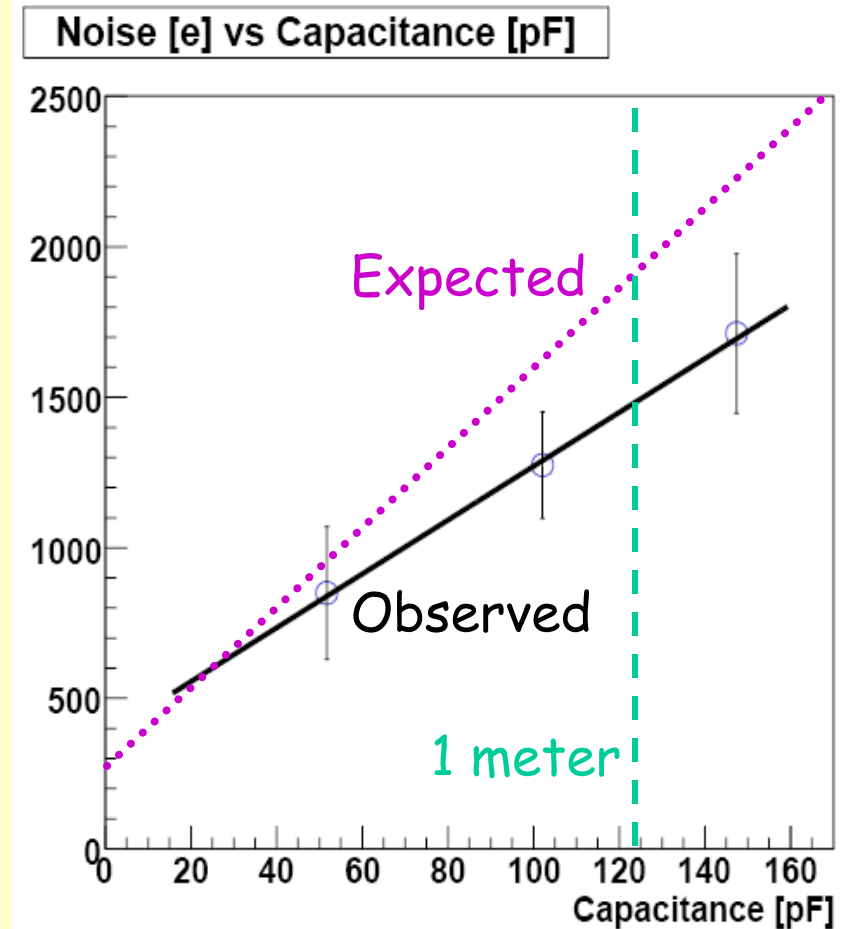
Measured dependence is roughly
(noise in equivalent electrons)

$$\sigma_{\text{noise}} = 375 + 8.9 * C$$

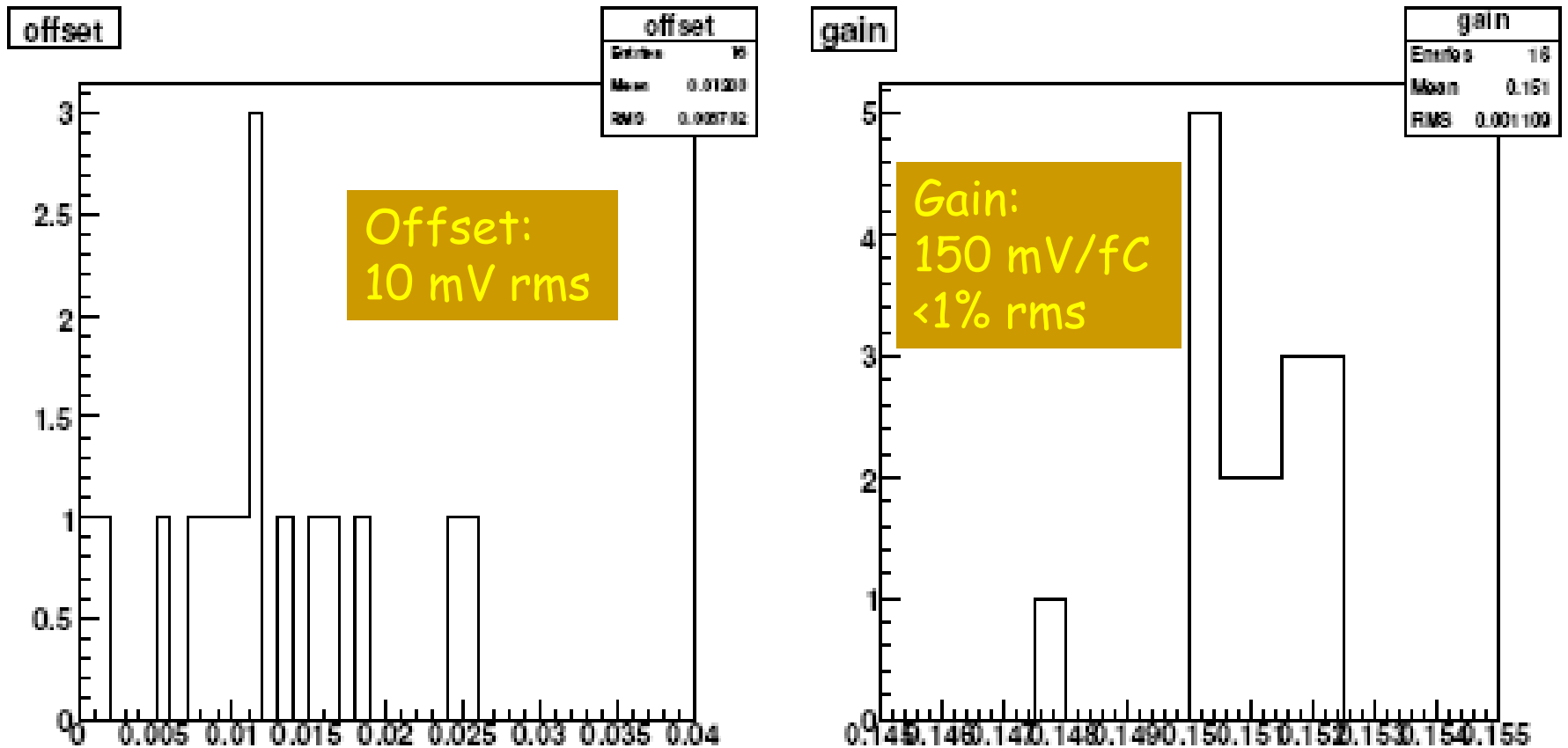
with C in pF.

Experience at $0.5 \mu\text{m}$ had suggested that model noise parameters needed to be boosted by 20% or so; these results suggest $0.25 \mu\text{m}$ model parameters are accurate

→ Noise performance somewhat better than anticipated.

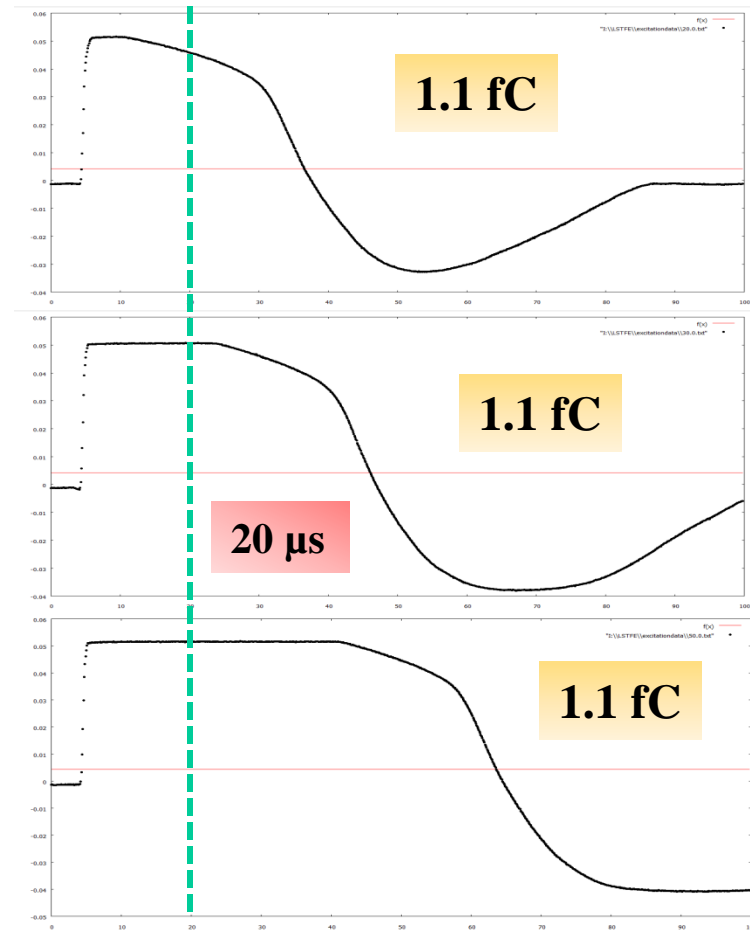
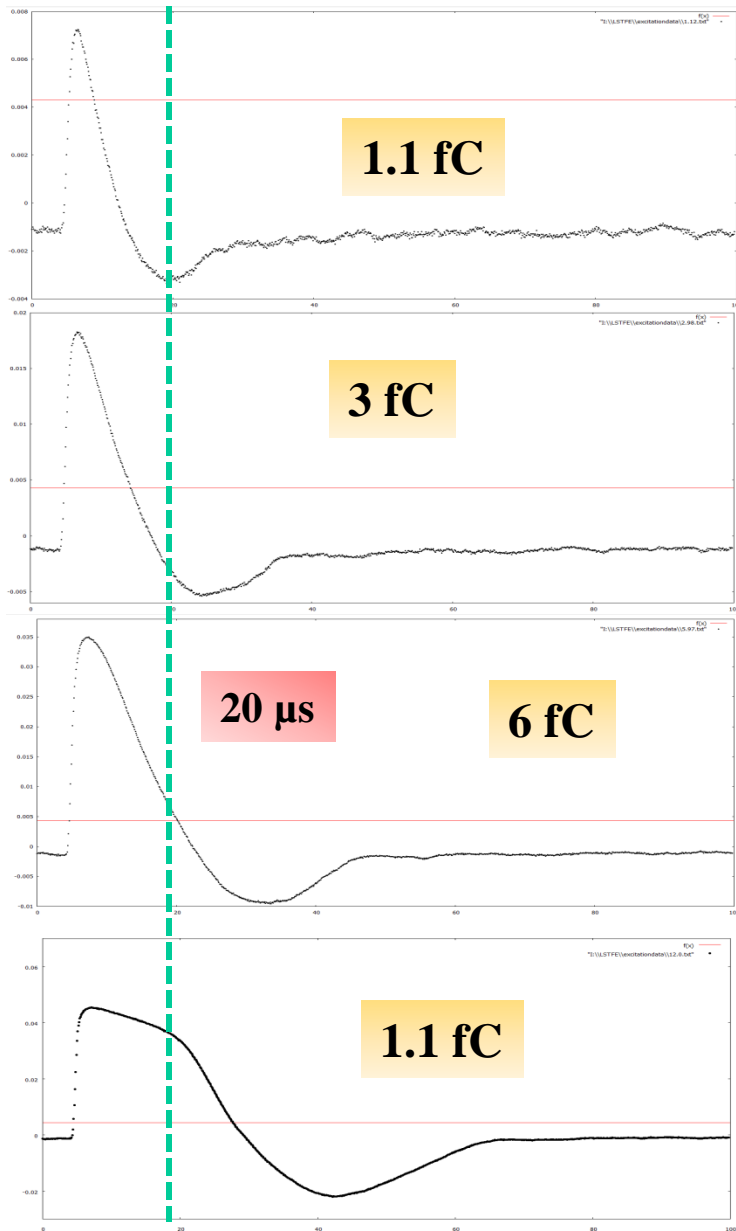


Channel-to-Channel Matching



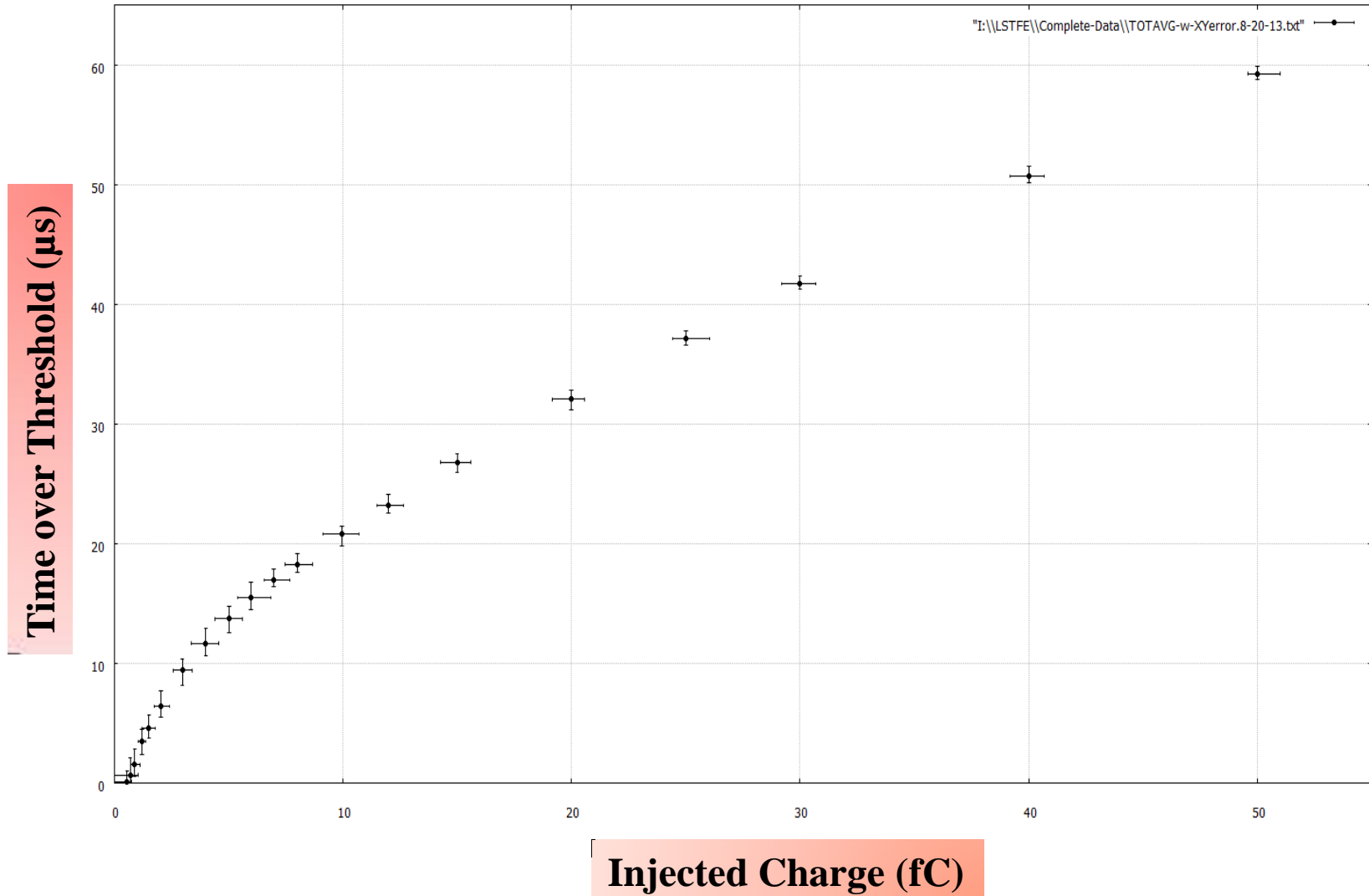
Occupancy threshold of 1.2 fC ($1875 e^-$) \rightarrow 180 mV
 ± 2 mV ($20 e^-$) from gain variation
 ± 10 mV ($100 e^-$) from offset variation

Evolution of LSTFE response against a fixed (0.7 fC) threshold

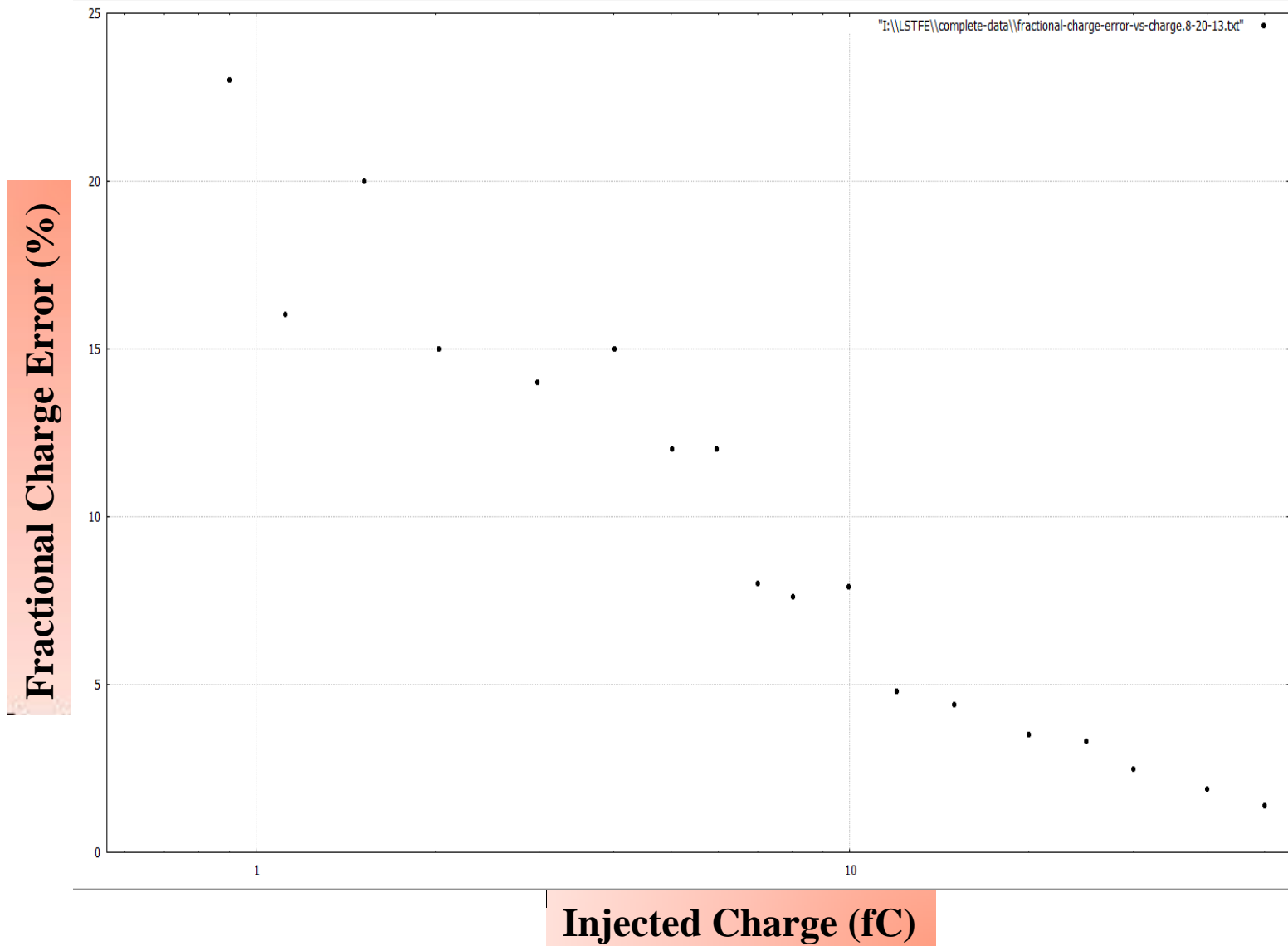


Return to baseline for typical (~ 3 fc) pulse:
40 μ s (directly related to shaping time!)

Time Over Threshold versus Injected Charge, and RMS spread



Resulting Fractional Charge Error



Electronics Simulation: Resolution

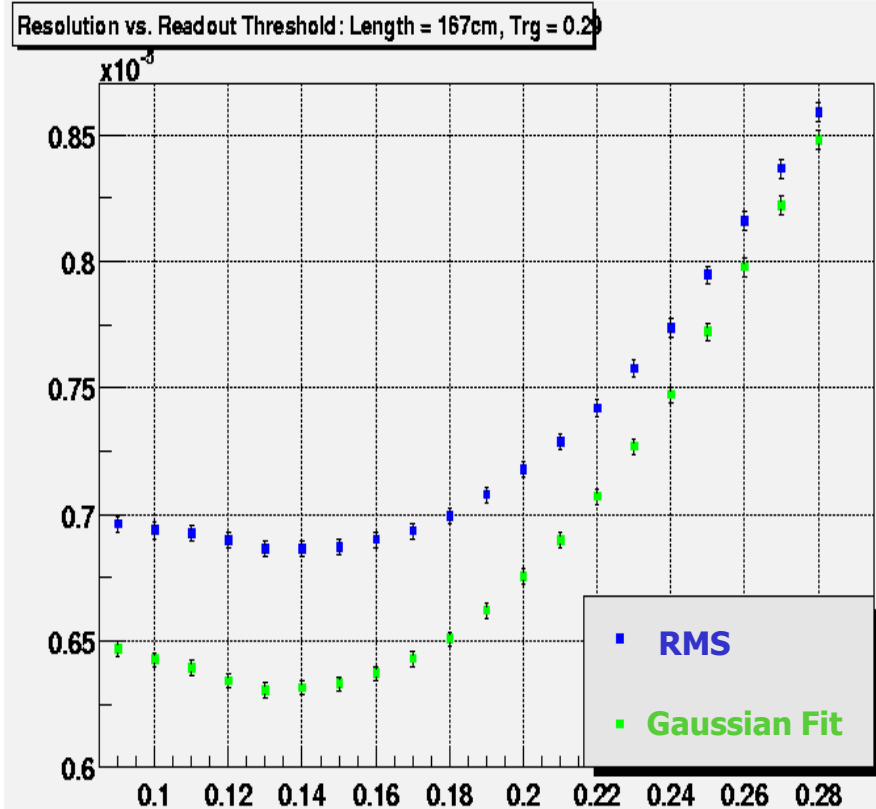
Detector Noise:

Capacitive contribution;
from SPICE simulation
normalized to bench tests
with GLAST electronics

Analog Measurement:

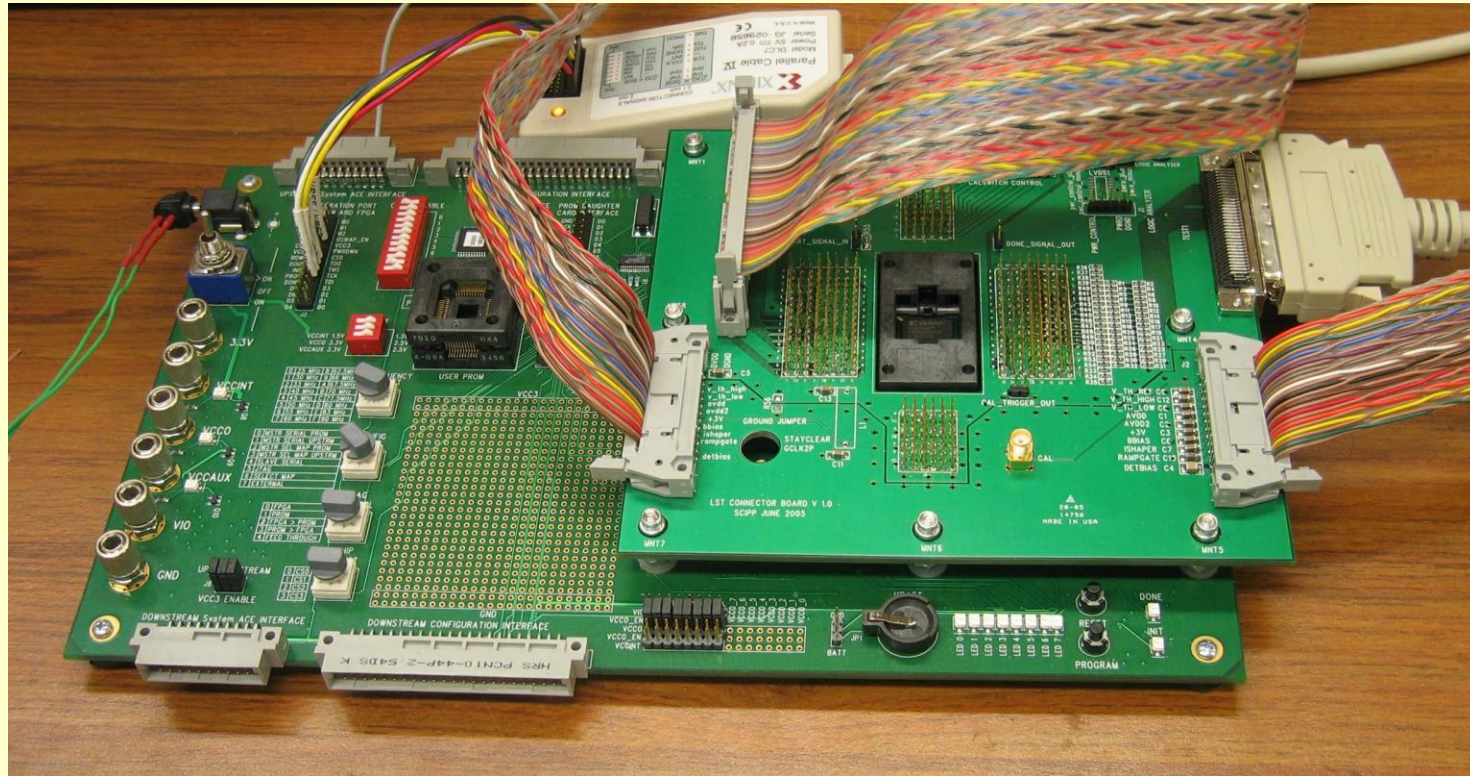
Provided by time-over-
threshold; lookup table
provides conversions back
into analog pulse height
(as for actual data)

Detector Resolution (units of $10\mu\text{m}$)



Lower (read) threshold in fraction of min-i
(High threshold is at 0.29 times min-i)

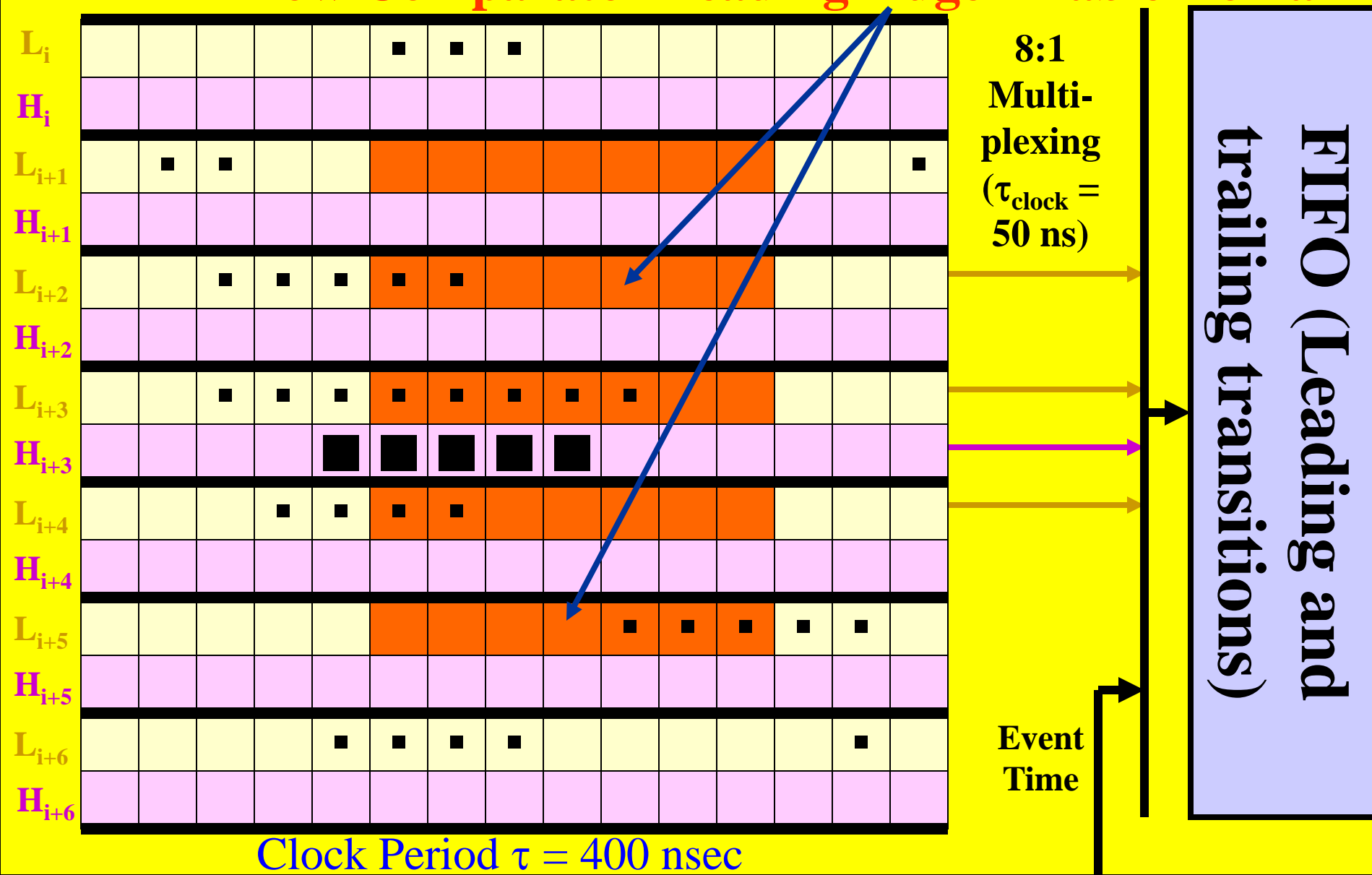
DIGITAL ARCHITECTURE: FPGA DEVELOPMENT



Digital logic under development on FPGA (Wang, Kroseberg), will be included on front-end ASIC after performance verified on test bench and in test beam.

Proposed LSTFE Back-End Architecture

Low Comparator Leading-Edge-Enable Domain



Note on LSTFE Digital Architecture

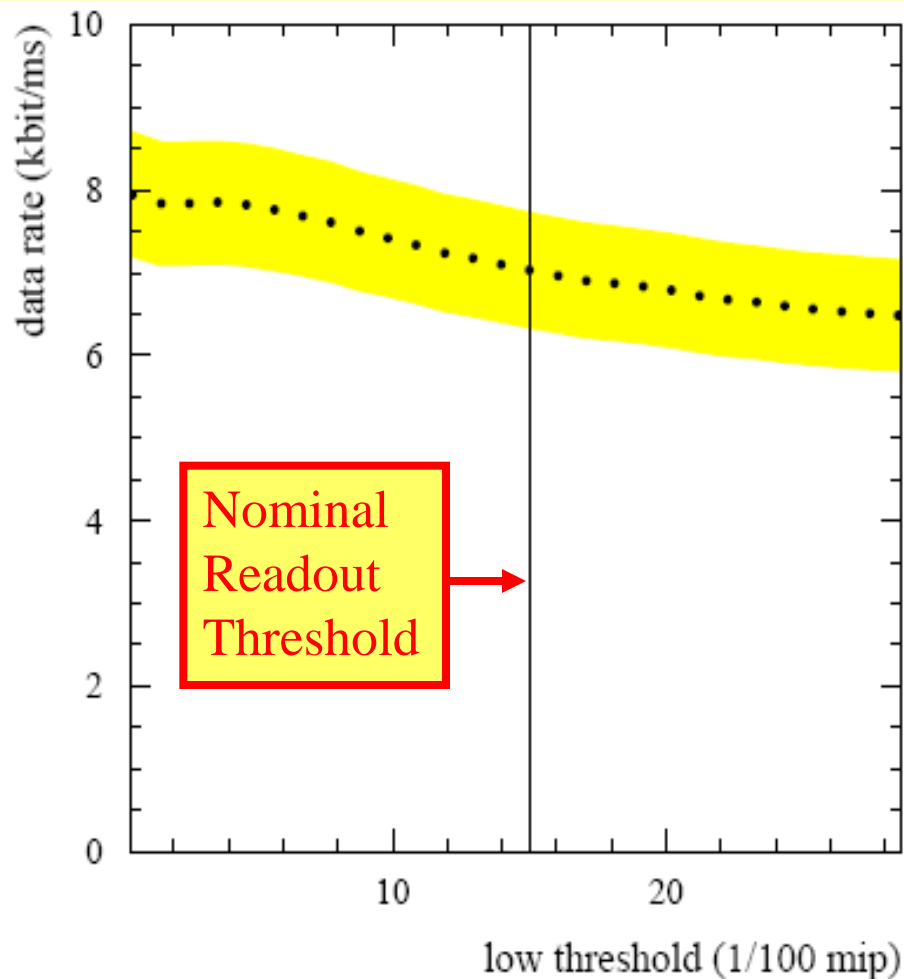
Use of time-over-threshold (vs. analog-to-digital conversion) permits real-time storage of pulse-height information.

→ No concern about buffering

→ LSTFE system can operate in arbitrarily high-rate environment; is ideal for (short ladder) forward tracking systems as well as long-ladder central tracking applications.

DIGITAL ARCHITECTURE SIMULATION

ModelSim package permits realistic simulation of FPGA code (signal propagation not yet simulated)



Simulate detector background (innermost SiD layer) and noise rates for 500 GeV running, as a function of read-out threshold.

Per 128 channel chip ~ 7 kbit per spill $\rightarrow 35$ kbit/second

For entire SiD tracker ~ 0.5 -5 GHz data rate, depending on ladder length ($\times 100$ data rate suppression)

Limitations on Microstrip Ladder Length

**International Workshop on Future Linear
Colliders**

University of Tokyo, 11-15 November 2013

Bruce Schumm

Santa Cruz Institute for Particle Physics

Study involved:

- Measurements of readout noise vs. strip load
- SPICE-level simulation of readout noise, including network effects
- Pulse-development simulation to determine operating point and length limitations

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journal homepage: www.elsevier.com/locate/nima



Microstrip electrode readout noise for load-dominated long shaping-time systems



Kelsey Collier, Taylor Cunnington, Sean Crosby, Vitaliy Fadeyev, Forest Martinez-McKinney,
Khilesh Mistry, Bruce A. Schumm*, Edwin Spencer, Aaron Taylor, Max Wilder

Santa Cruz Institute for Particle Physics and the University of California, Santa Cruz, CA 95064, United States

Standard Form for Readout Noise (Spieler)

The diagram shows the equation for readout noise Q^2 with several annotations. A green box labeled 'Parallel Resistance' has a green arrow pointing to the $\frac{4kT}{R_B}$ term. A green box labeled 'Series Resistance' has a green arrow pointing to the $4kTR_s$ term. A green box labeled 'Amplifier Noise (parallel)' has a green arrow pointing to the i_{na}^2 term. A green box labeled 'Amplifier Noise (series)' has a green arrow pointing to the e_{na}^2 term. A red circle highlights the term $\frac{F_v C^2}{\tau} (4kTR_s + e_{na}^2)$, and an orange box below it with a red arrow pointing to the circle contains the text 'Dominant term for long ladders (grows as $L^{3/2}$)'.

$$Q^2 = F_i \tau \left(2eI_d + \frac{4kT}{R_B} + i_{na}^2 \right) + \frac{F_v C^2}{\tau} (4kTR_s + e_{na}^2) + 4F_v A_f C^2$$

Parallel Resistance

Series Resistance

Amplifier Noise (parallel)

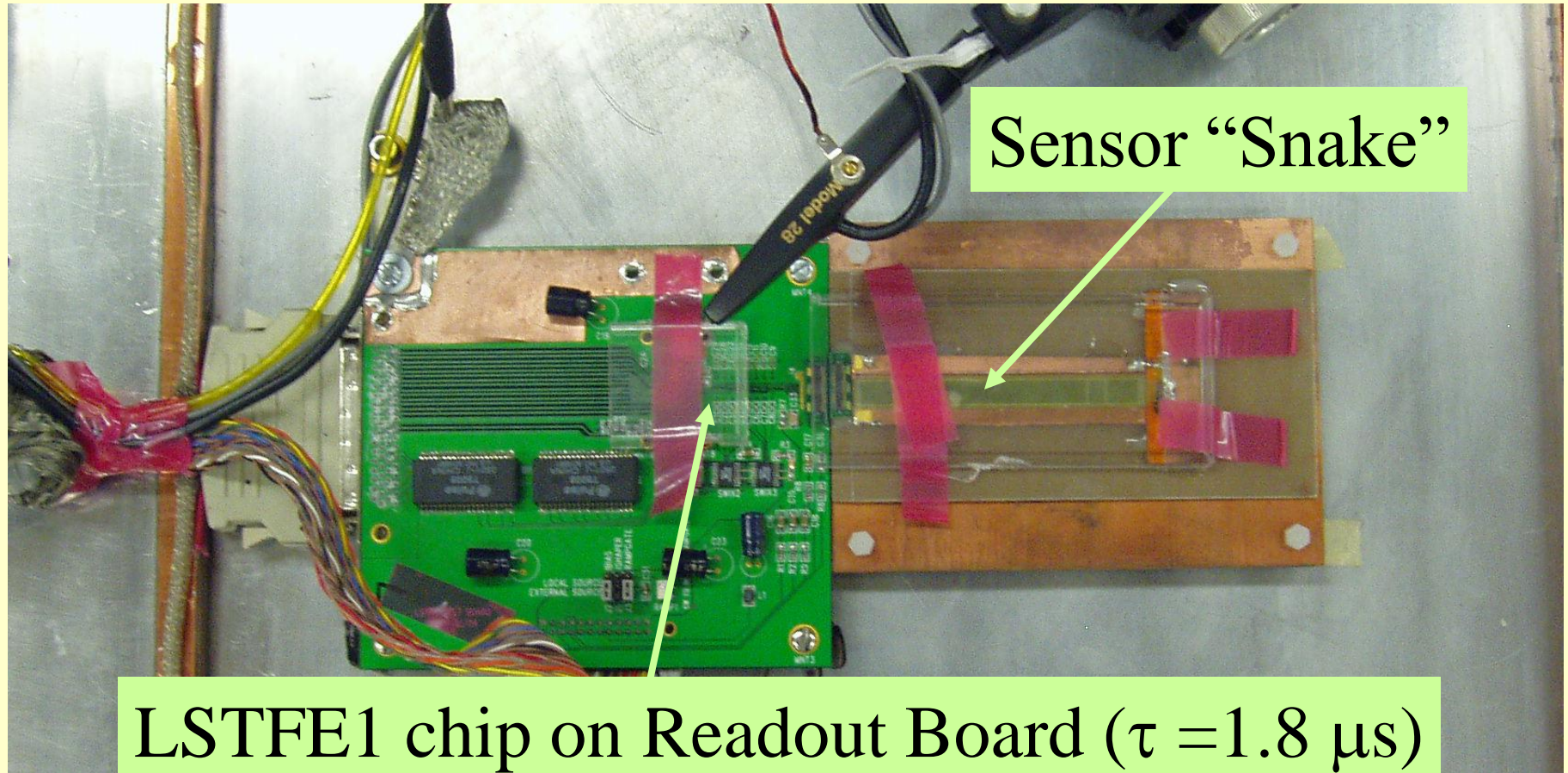
Amplifier Noise (series)

Dominant term for long ladders (grows as $L^{3/2}$)

F_i , F_v are signal shape parameters that can be determined from average scope traces.

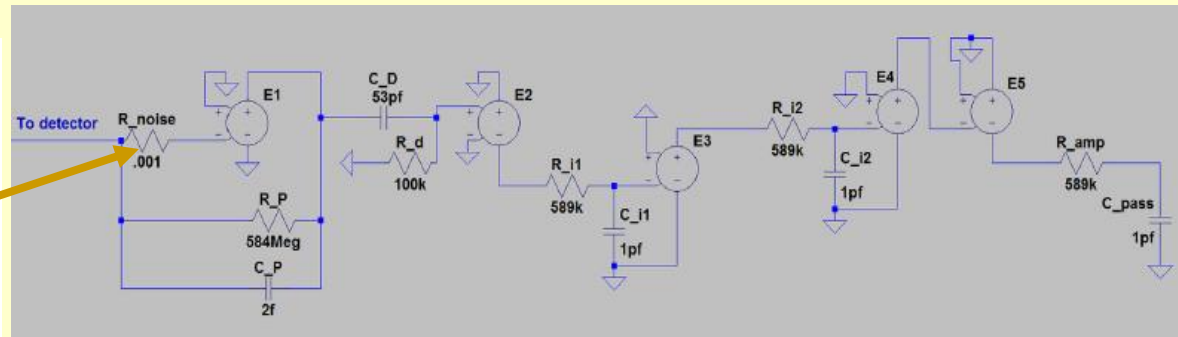
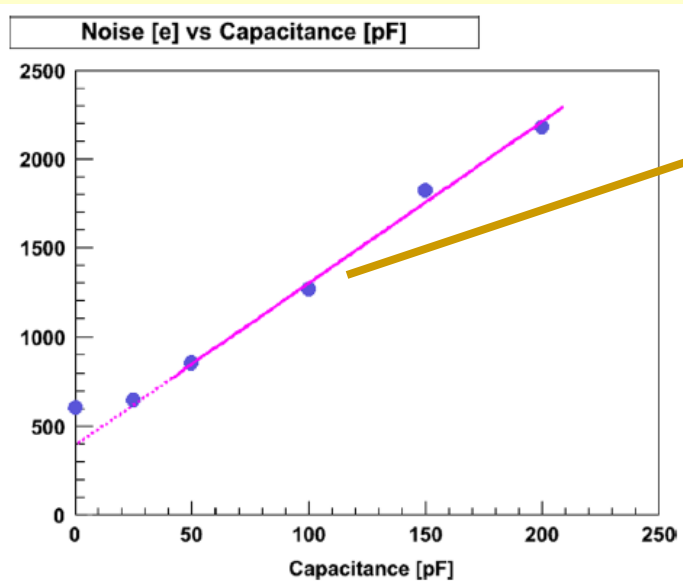
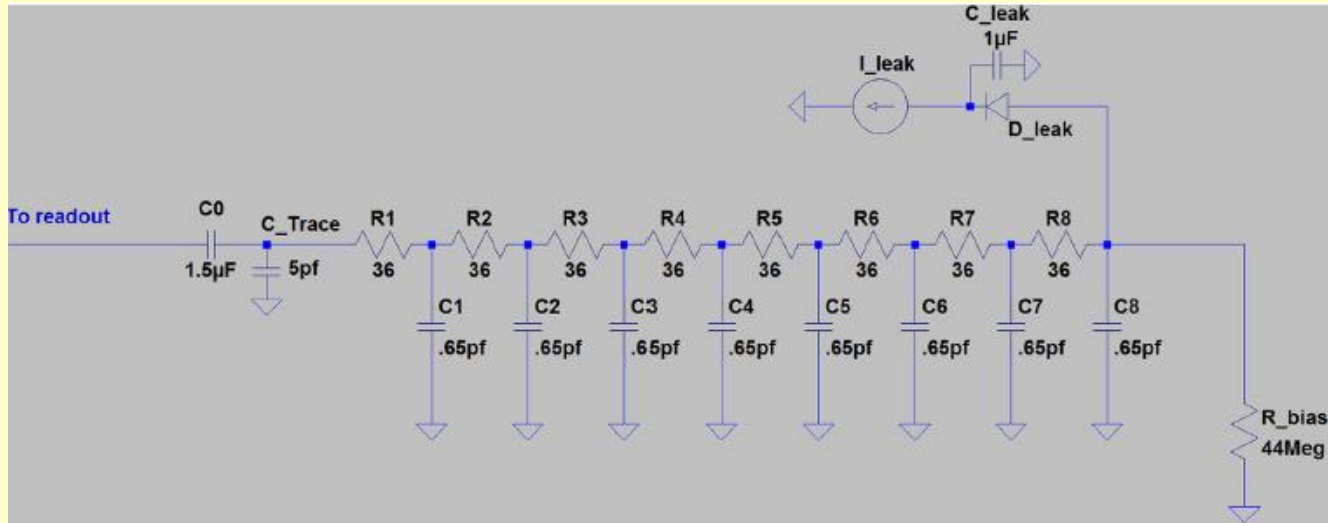
➔ Expression assumes single, lumped R, C load element; in fact, microstrip electrode is a **distributed network**

Sensor “Snake”: Read out up to 13 daisy-chained
5cm sensors (with LSTFE-1 ASIC)



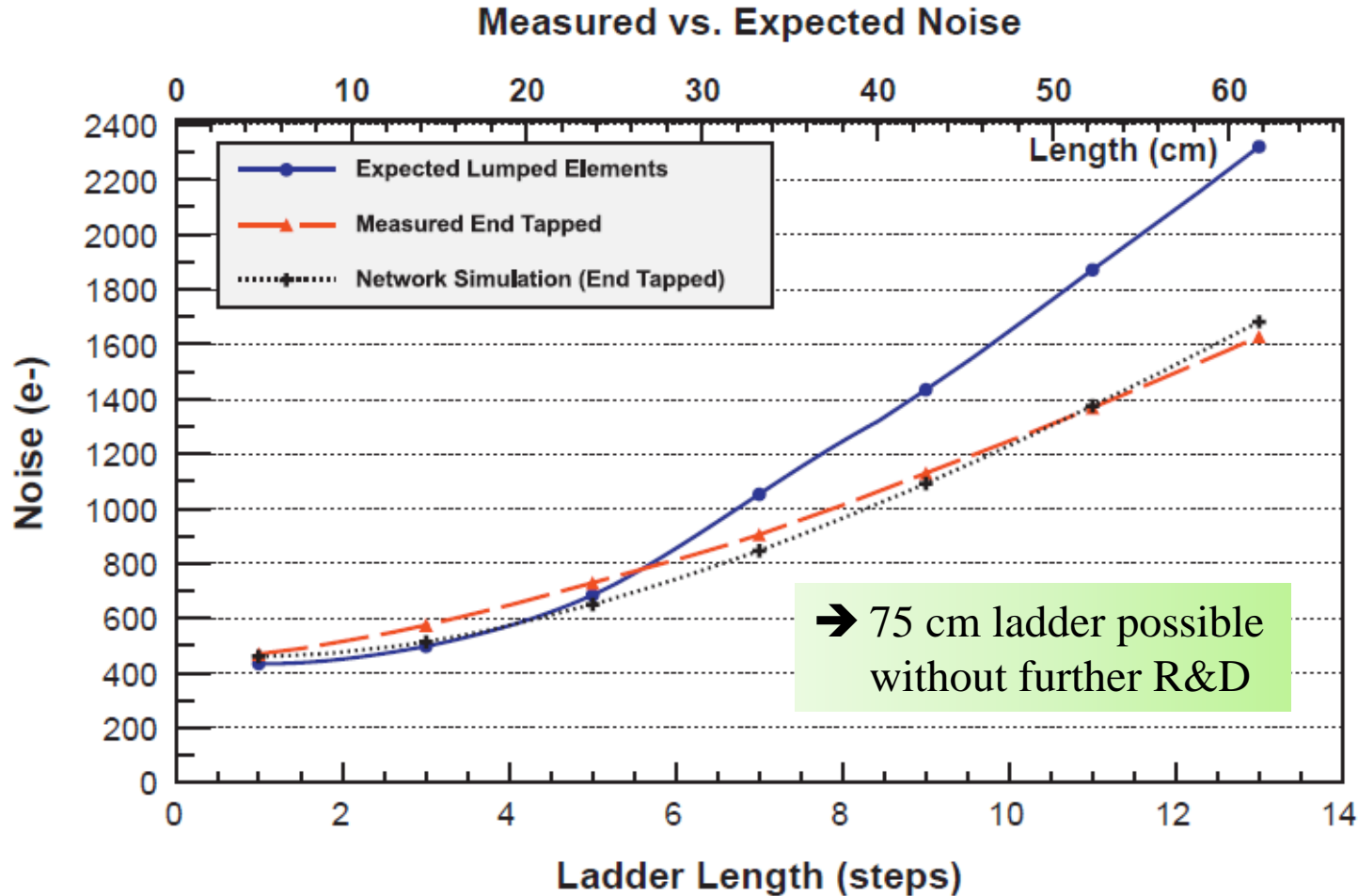
**Can read out from end, or from middle of
chain (“center-tap”)**

Simulation: Each “rung” (strip) divided into 8 discrete pieces; equivalent to continuous network.



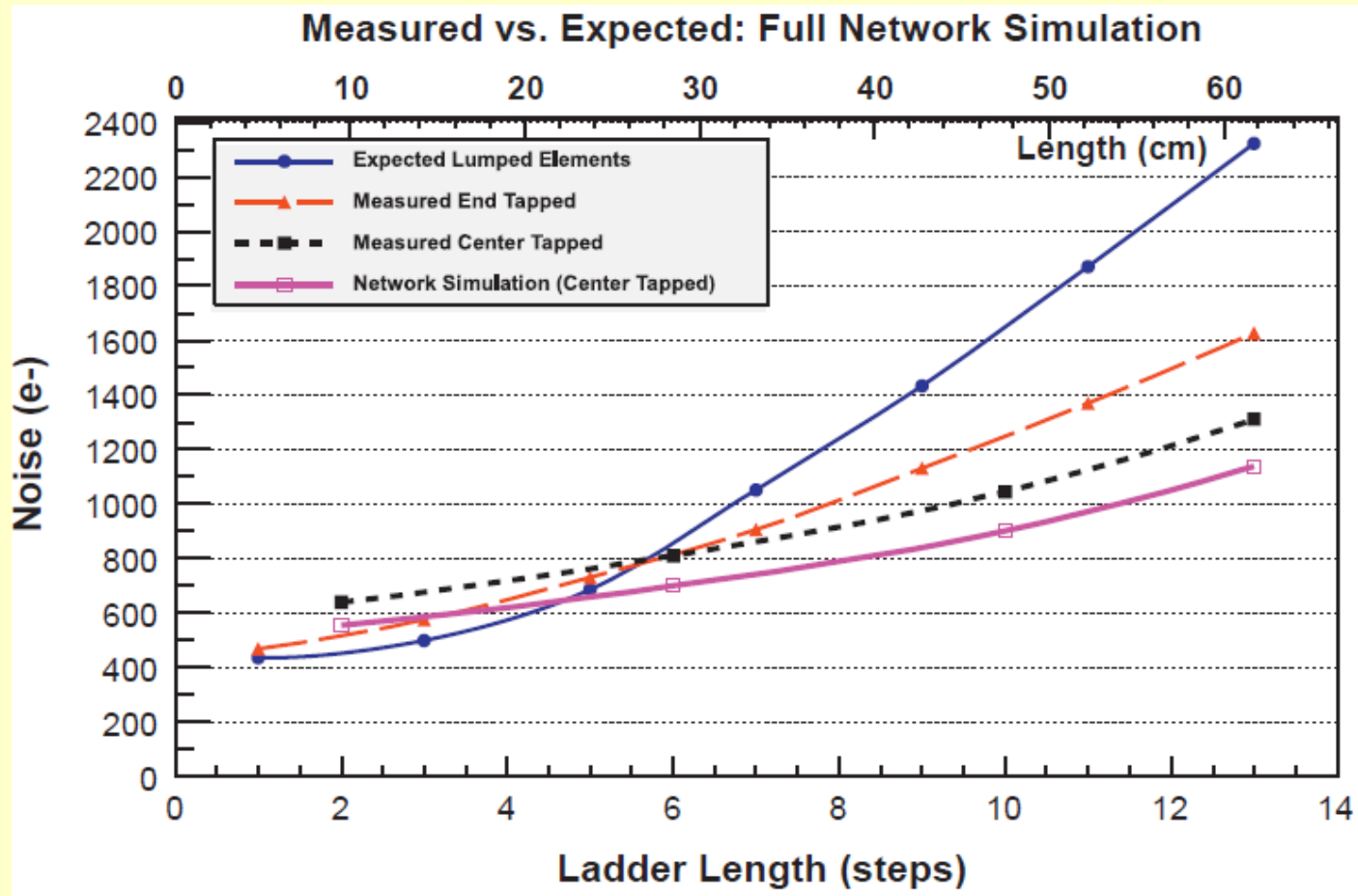
Readout (LSTFE) noise matched to noise calibration with purely capacitive load via small finite-temperature resistor

End Read-Out Results



- Good agreement between simulation and measurement
- Significant mitigation of noise by network (good news!)

Center Read-Out Results



- Additional mitigation of noise (more good news)
- Not quite as helpful as expected (?)

SUMMARY

- The LSTFE ASIC is designed for generic ILC microstrip readout
- Features real-time readout via time-over-threshold
- $\sim 20 \mu\text{s}$ recovery time can be lessened for short forward strips by reducing shaping time
- Relative simple (reliability, yield)
- Further work: implement power-cycling, develop digital back end [optimize shaping time for short strips]
- Long ladders: can reach $\sim 1\text{m}$ with center readout and/or thicker, wider microstrip traces

RANDOM BACK-UP SLIDES

Note About LSTFE Shaping Time

Original target: $\tau_{\text{shape}} = 3 \mu\text{sec}$, with some controlled variability ("ISHAPR")

→ Appropriate for long (2m) ladders

In actuality, $\tau_{\text{shape}} \sim 1.5 \mu\text{sec}$; tests are done at $1.2 \mu\text{sec}$, closer to optimum for SLAC short-ladder approach

Difference between target and actual shaping time understood in terms of simulation (full layout)

LSTFE-2 will have $3 \mu\text{sec}$ shaping time

Power Cycling

Idea: Latch operating bias points and isolate chip from outside world.

- Per-channel power consumption reduces from ~ 1 mW to ~ 1 μ W.
- Restoration to operating point should take ~ 1 msec.

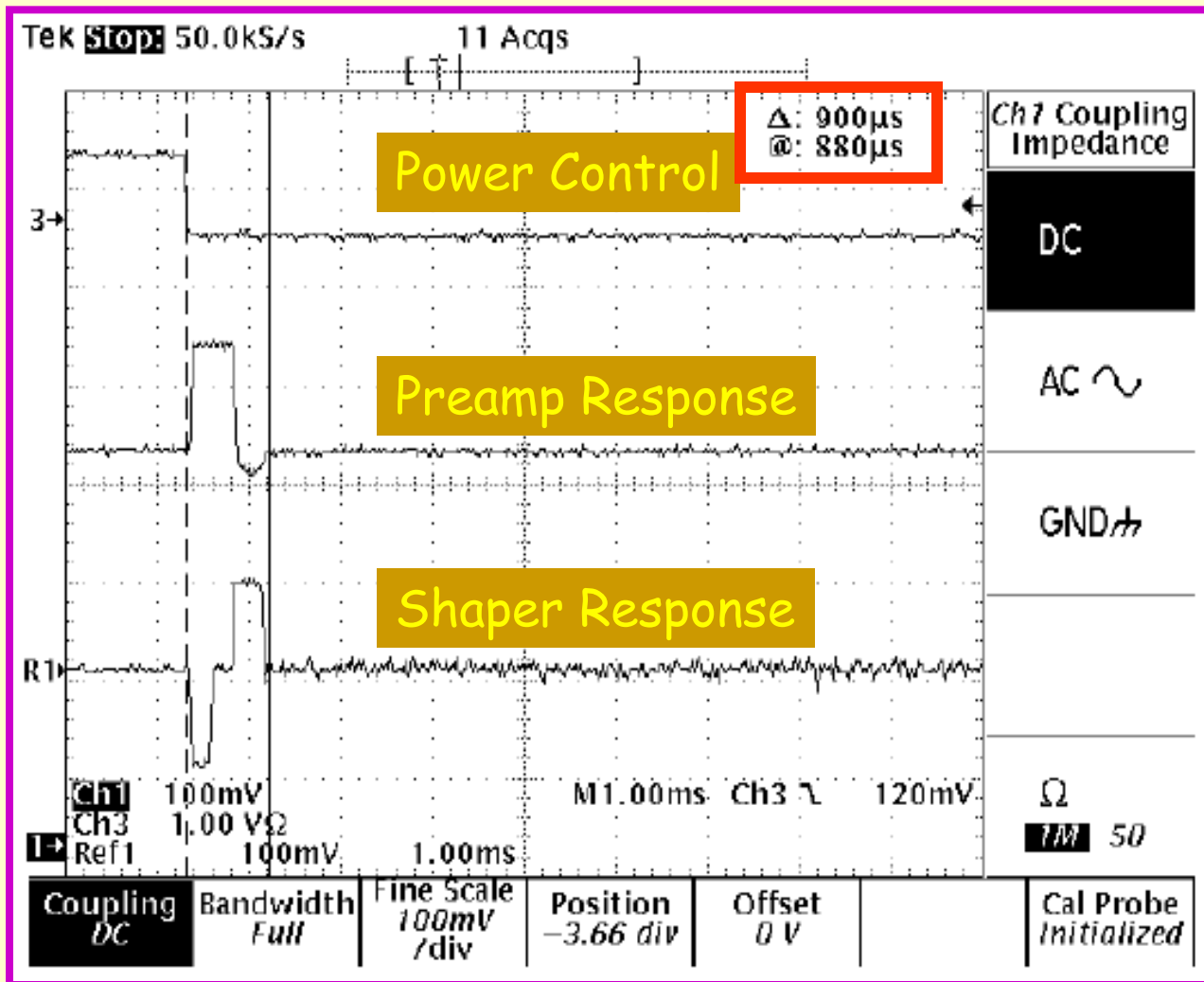
Current status:

- Internal leakage (protection diodes + ?) degrades latched operating point
- Restoration takes ~ 40 msec ($\times 5$ power savings)
- Injection of small current (< 1 nA) to counter leakage allows for 1 msec restoration.

Future (LSTFE-2)

- Low-current feedback will maintain bias points; solution already incorporated in LSTFE-2 design

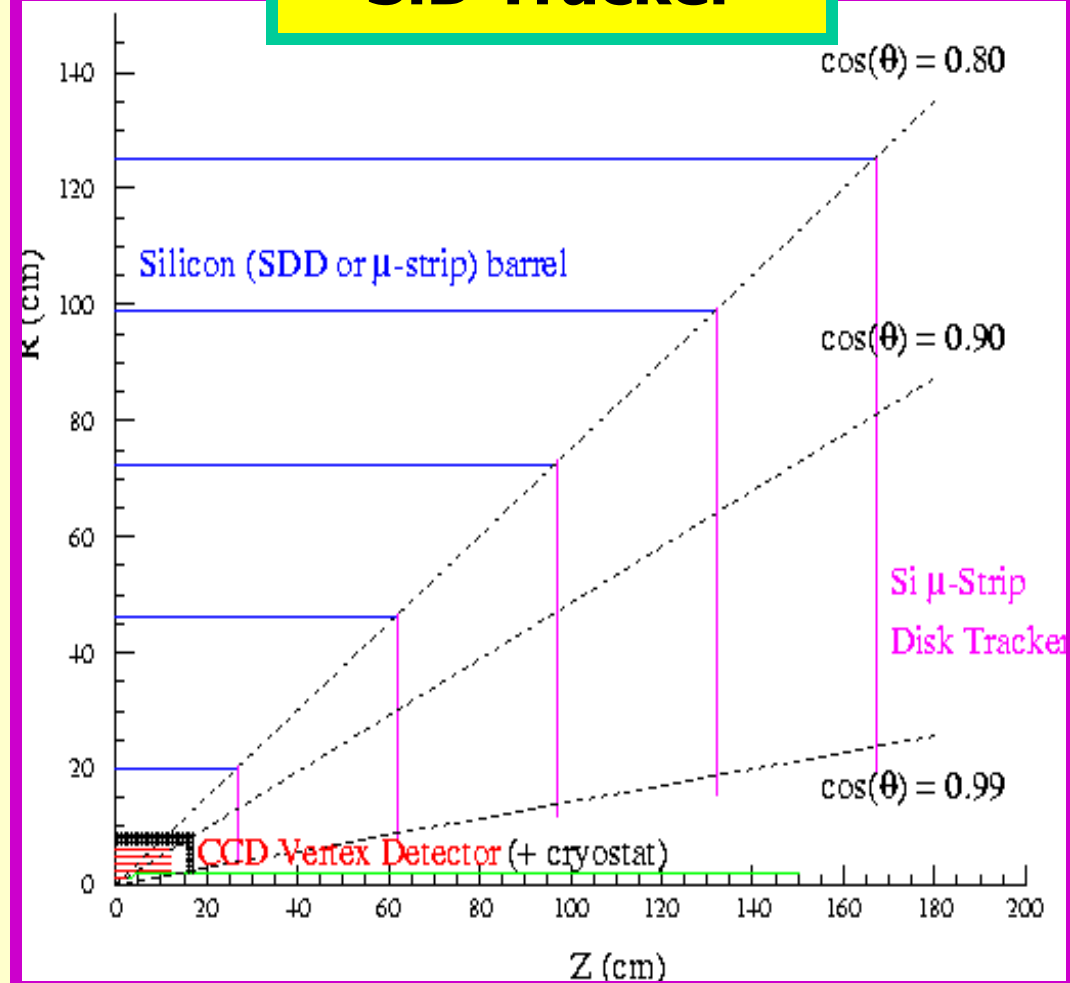
Power Cycling with Small Injected Current



Solution in hand to maintain bias levels in "off" state with low-power feedback; will eliminate need for external trickle current

Silicon Microstrip Readout R&D

SiD Tracker



Initial Motivation

Exploit long shaping time (low noise) and power cycling to:

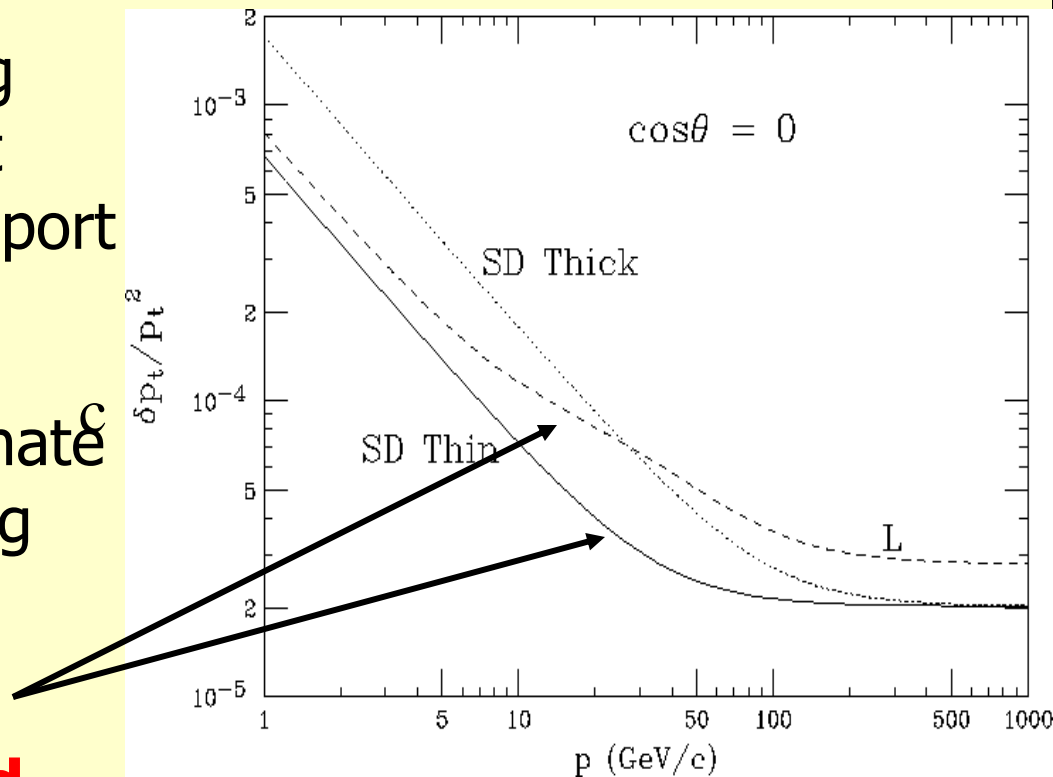
- Remove electronics and cabling from active area (long ladders)
- Eliminate need for active cooling

The Gossamer Tracker

Ideas:

- Low noise readout → Long ladders → substantially limit electronics readout and support
- Thin inner detector layers
- Exploit duty cycle → eliminate need for active cooling

Competitive with gaseous tracking over full range of momentum (also: **forward region**)



Alternative: shorter ladders, but better point resolution

LSTFE-2 DESIGN

LSTFE-1 gain rolls off at ~ 10 mip; are instituting log-amp design (50 mip dynamic range)

Power cycling sol'n that cancels (on-chip) leakage currents

Improved environmental isolation

Additional amplification stage (noise, shaping time, matching

Improved control of return-to-baseline for < 4 mip signals

Multi-channel (64? 128? 256?) w/ 8:1 multiplexing of output

Must still establish pad geometry (sensor choice!)